

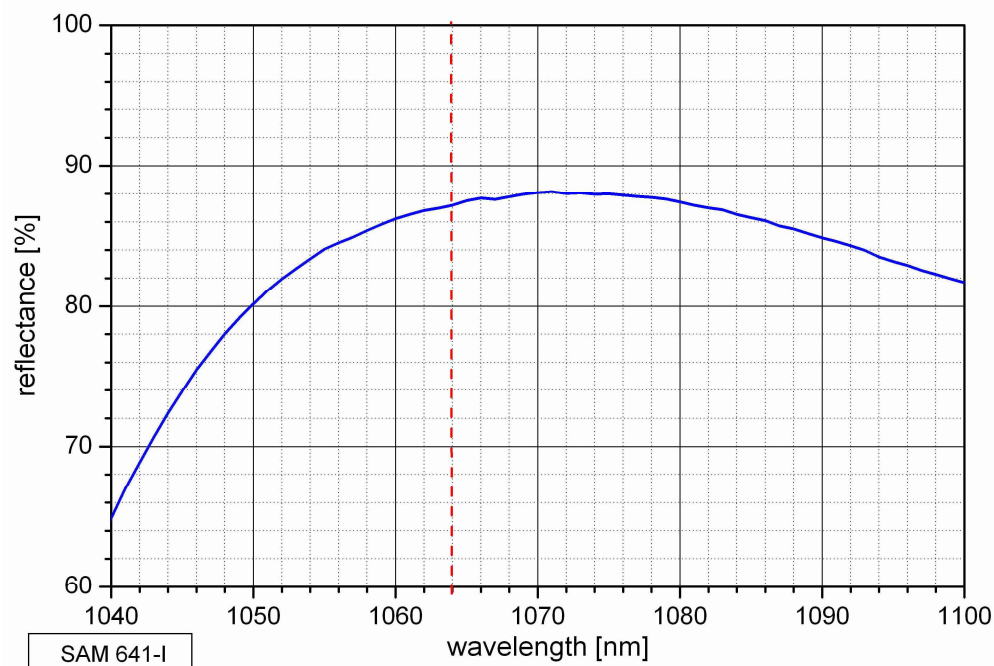
SAM™ Data Sheet SAM-1064-13-124ps-x, $\lambda = 1064 \text{ nm}$

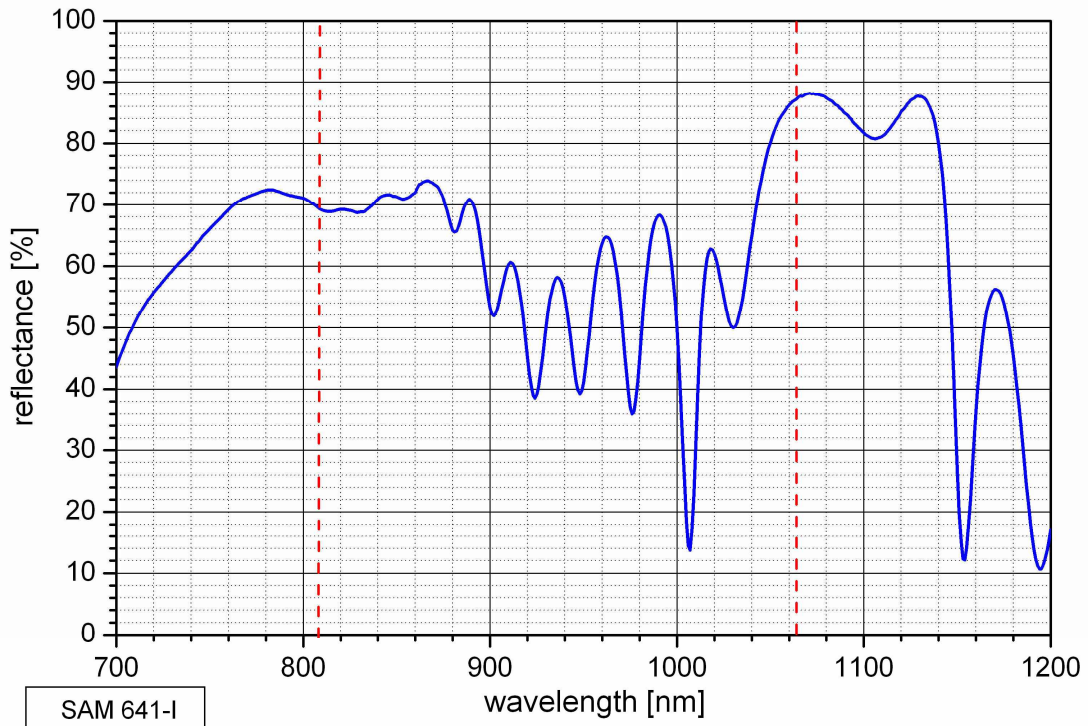
Laser wavelength	$\lambda = 1064 \text{ nm}$
High reflection band	$\lambda = 1050 \dots 1100 \text{ nm}$
Reflectance at 808 nm	$R_{808} = 70 \%$
Absorbance	$A_0 = 13 \%$
Modulation depth	$\Delta R = 7 \%$
Non-saturable loss	$A_{ns} = 6 \%$
Saturation fluence	$\Phi_{sat} = 130 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 124 \text{ ps}$
Damage threshold	$\Phi = 2.5 \text{ mJ}/\text{cm}^2$
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 μm
Dielectric coating	HR @ 808 nm and AR @ 1064 nm

Mounting option **x** denotes the type of mounting as follows:

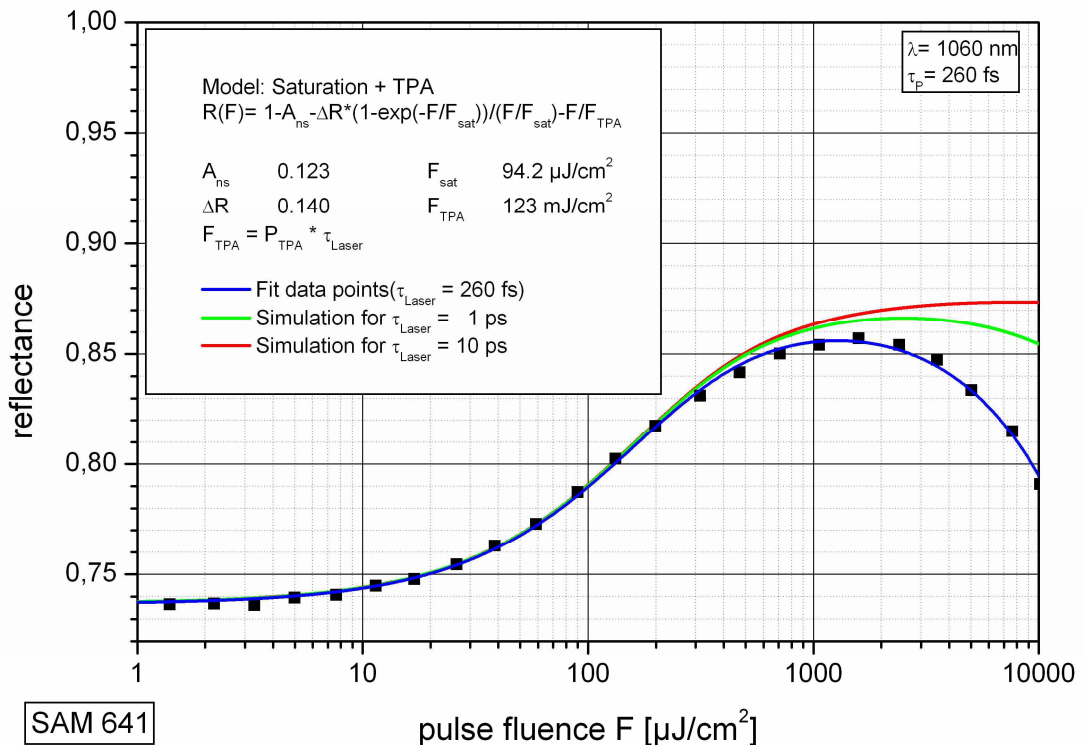
x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm \varnothing
x = 25.4 g	glued on a copper heat sink with 25.4 mm \varnothing
x = 12.7 s	soldered on a copper heat sink with 12.7 mm \varnothing
x = 25.4 s	soldered on a copper heat sink with 25.4 mm \varnothing
x = 25.4 w	soldered on a water cooled copper heat sink with 25.4 mm \varnothing
x = FC	mounted on a 1 m single mode fiber cable with FC connector

Low intensity spectral reflectance





Saturation measurement without dielectric coating



The saturation measurement has been done using a pulsed laser source with 260 fs pulse duration. Due to the high peak power density the two photon absorption (TPA) is significant in this case. The green and red curves are simulated for the same pulse fluences, but longer pulse durations of 1 ps and 10 ps respectively..

Pump-probe measurement

